

General Description:

The LWN3012BD3 uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN3.3*3.3-8L, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

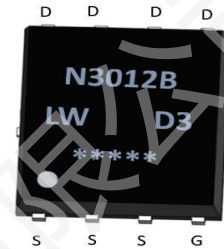
100% DVDS Tested

100% Avalanche Tested

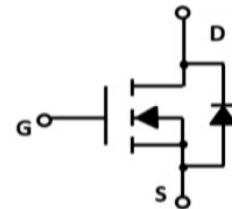


V_{DSS}	30	V
I_D	38	A
P_D	20	W
$R_{DS(ON)}$ TYPE	5.0	mΩ

Marking and Pin Assignment



Inner Equivalent Principium Chart



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
N3012B/LW D3/D.C.	LWN3012BD3	PDFN3.3*3.3-8L	Reel	5000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		30	V
I_D	Continuous Drain Current	$T_C=25^{\circ}C$	38	A
	Continuous Drain Current	$T_C=100^{\circ}C$	24	A
I_{DM}^{a1}	Pulsed Drain Current		152	A
E_{AS}^{a2}	Single pulse avalanche energy		76	mJ
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		20	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}C$
T_L	Maximum Temperature for Soldering		260	$^{\circ}C$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	6.25	$^{\circ}C/W$

Electrical Characteristic ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=30V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=15A$	--	5.0	6.5	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=4.5V, I_D=10A$	--	7.5	11	$m\Omega$

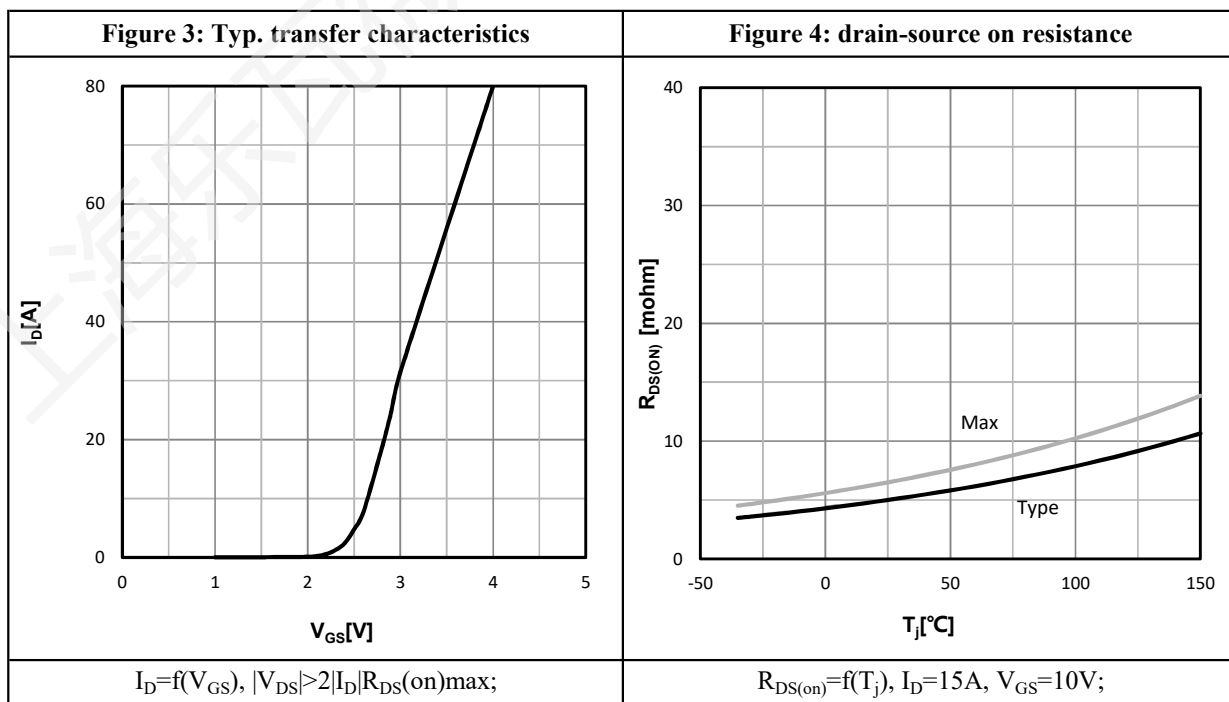
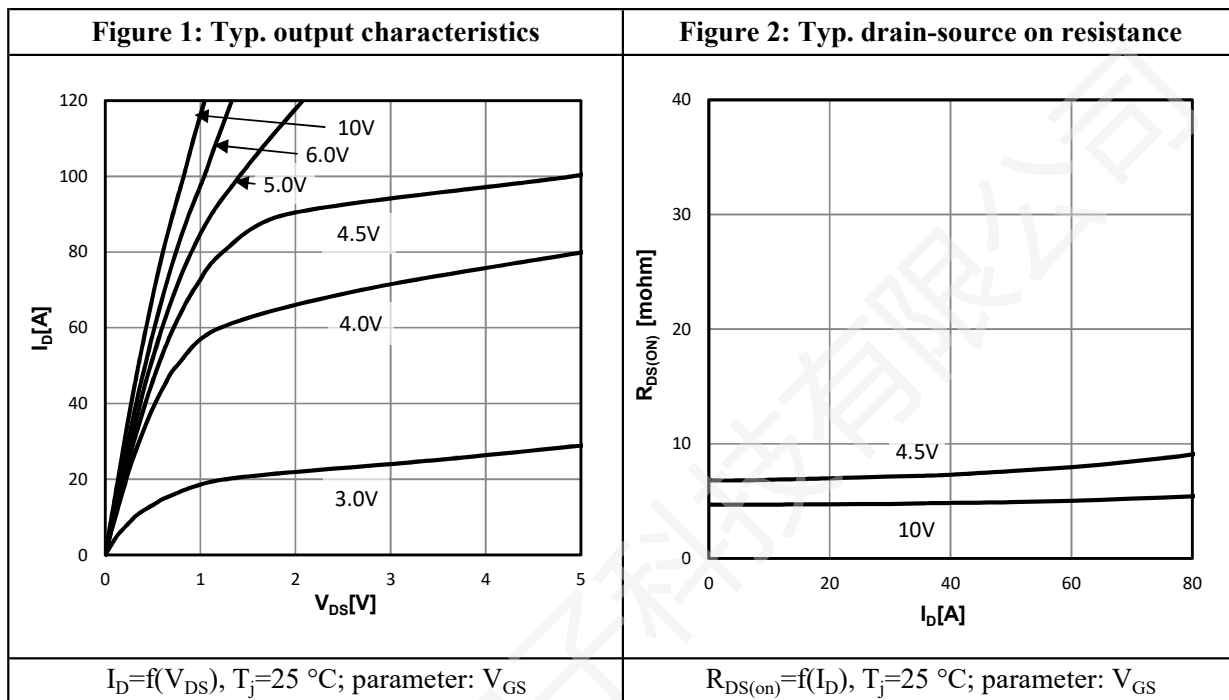
Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	--	1237	--	pF
C_{oss}	Output Capacitance	$V_{DS} = 15V$	--	180	--	
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	160	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0MHz$	--	1.7	--	Ω

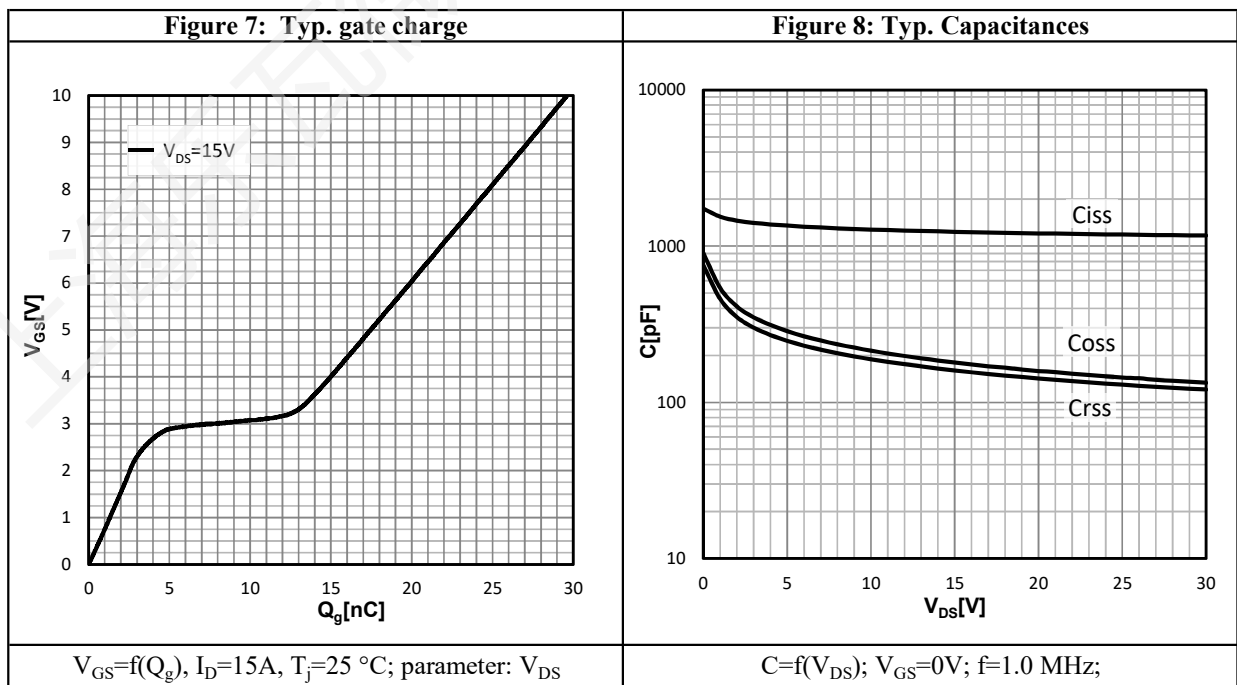
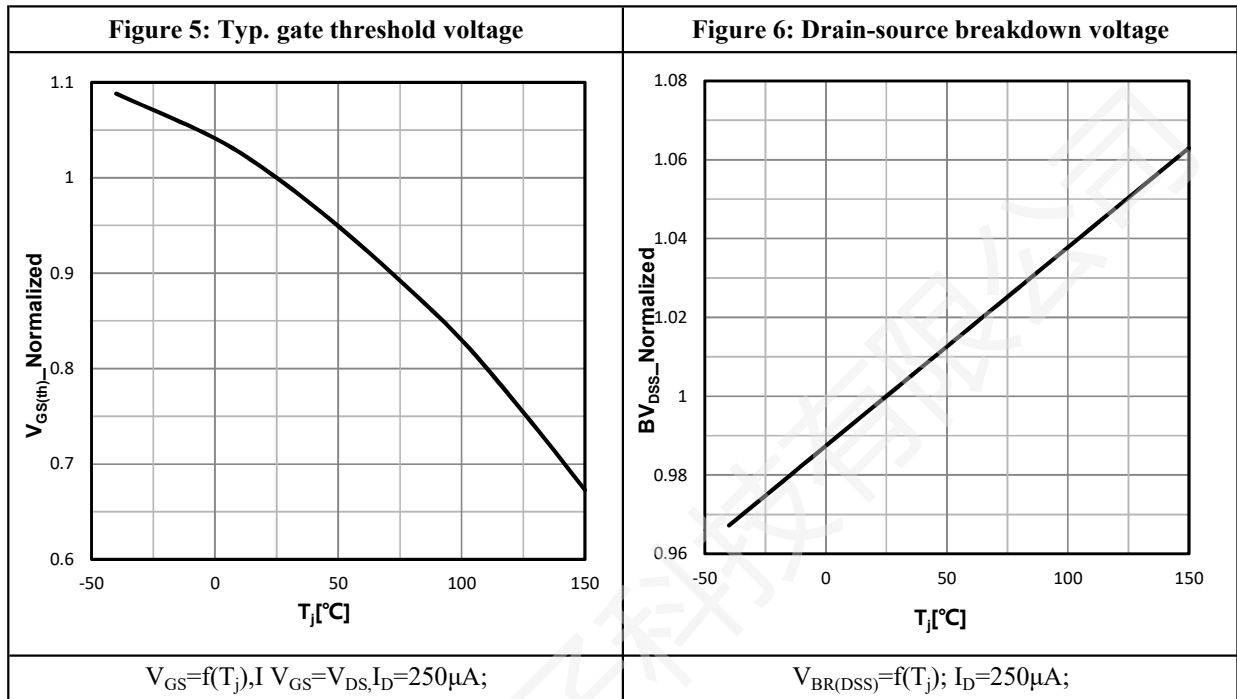
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = 15A$	--	5.0	--	ns
t_r	Rise Time	$V_{DS} = 15V$	--	11	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS} = 10V$	--	13	--	
t_f	Fall Time	$R_G = 3.0\Omega$	--	6.0	--	
Q_g	Total Gate Charge	$V_{GS} = 10V$	--	30	--	nC
Q_{gs}	Gate Source Charge	$V_{DS} = 15V$	--	4.0	--	
Q_{gd}	Gate Drain Charge	$I_D = 15A$	--	8.2	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C = 25\text{ }^{\circ}\text{C}$	--	--	38	A
V_{SD}	Diode Forward Voltage	$I_S=15A, V_{GS}=0V$	--	--	1.2	V

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $V_{DD}=15V, L=0.1mH, R_G=25\Omega$, Starting $T_J=25\text{ }^{\circ}\text{C}$

Characteristics Curve:




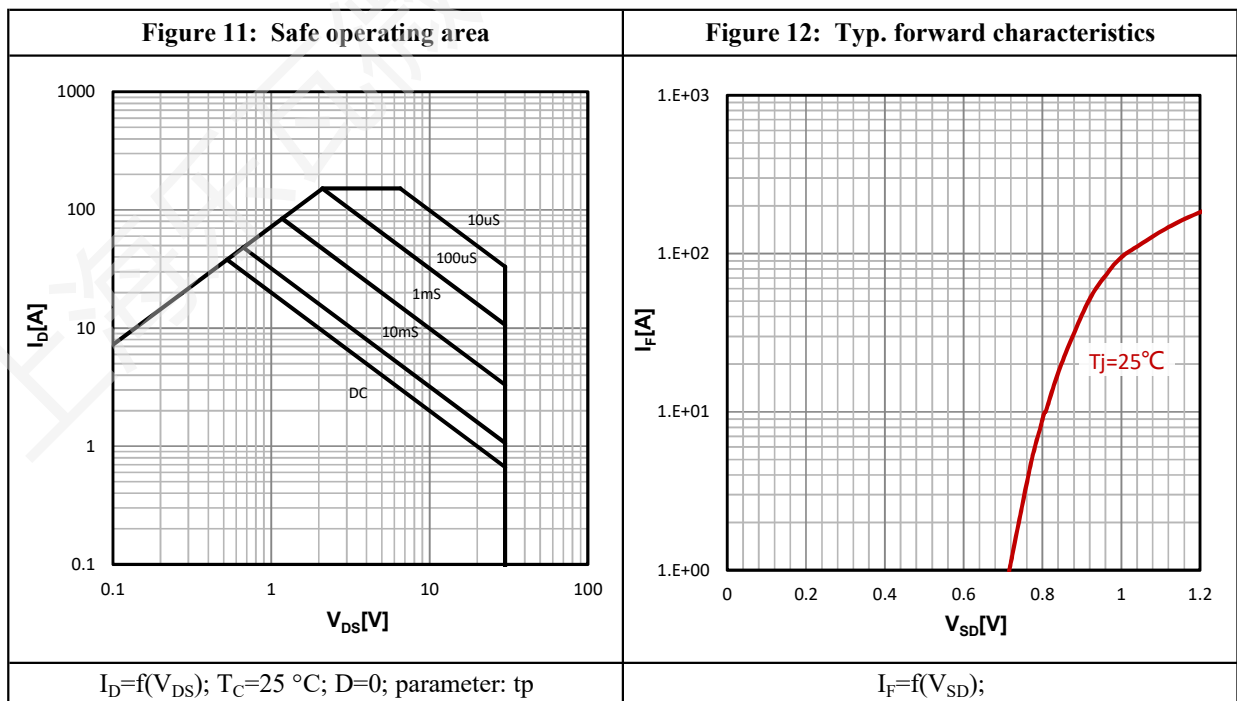
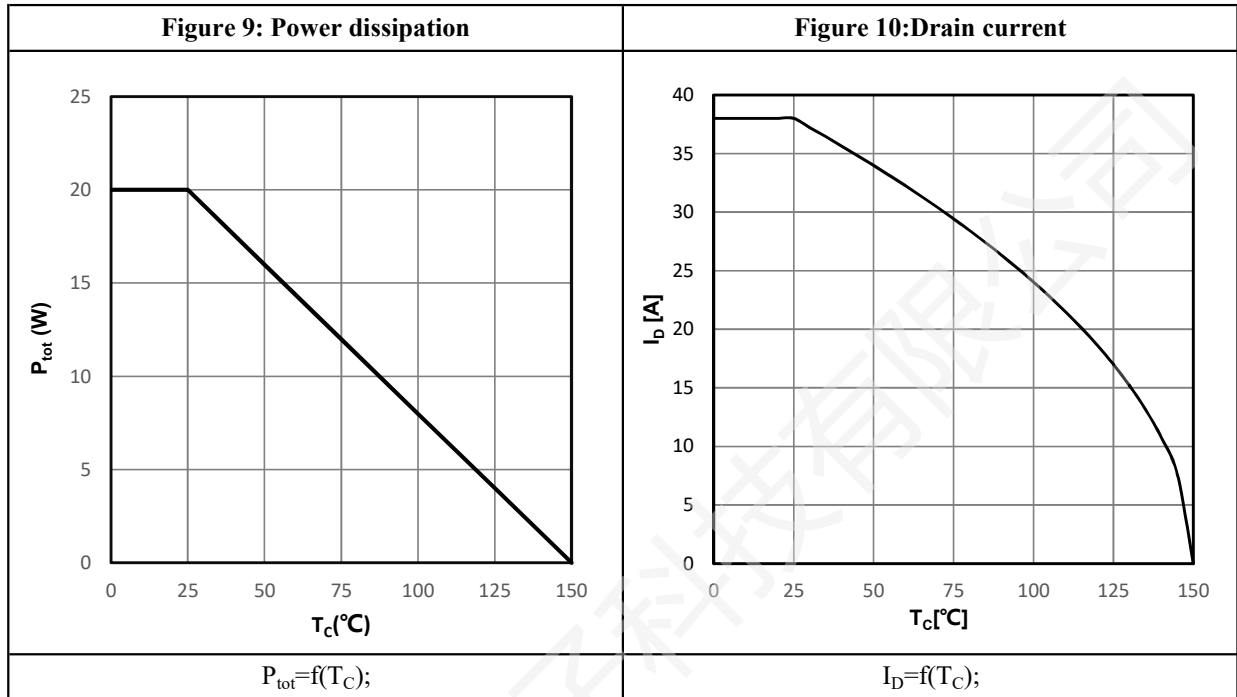
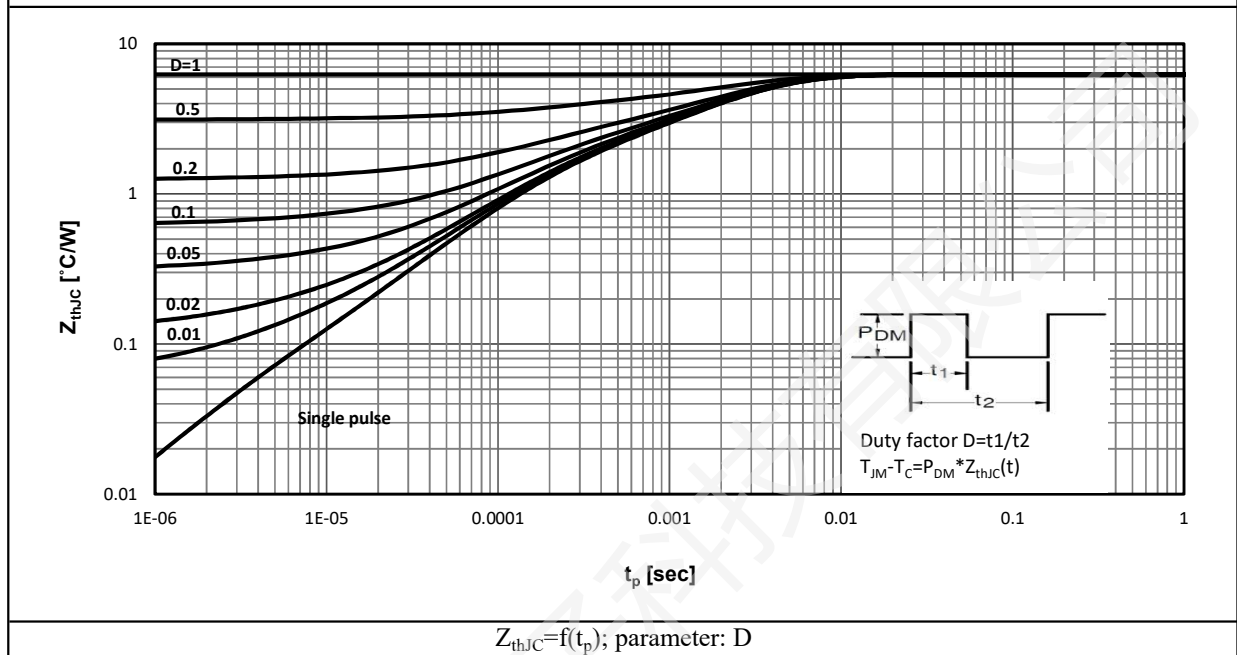
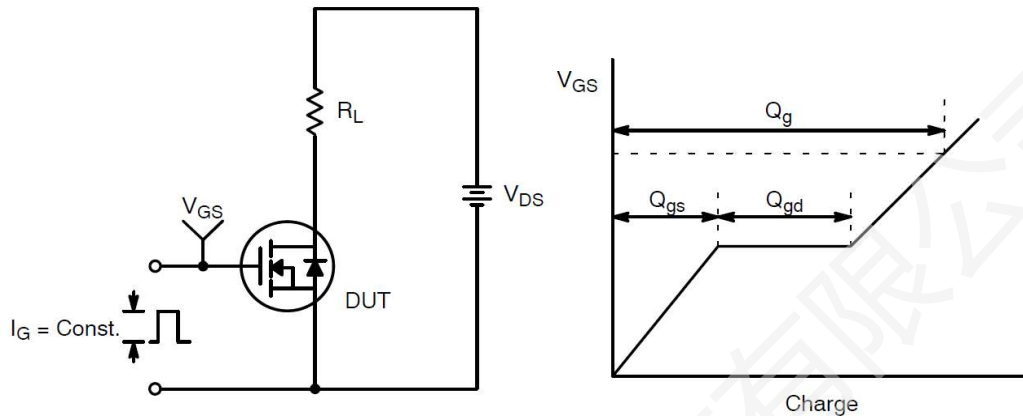
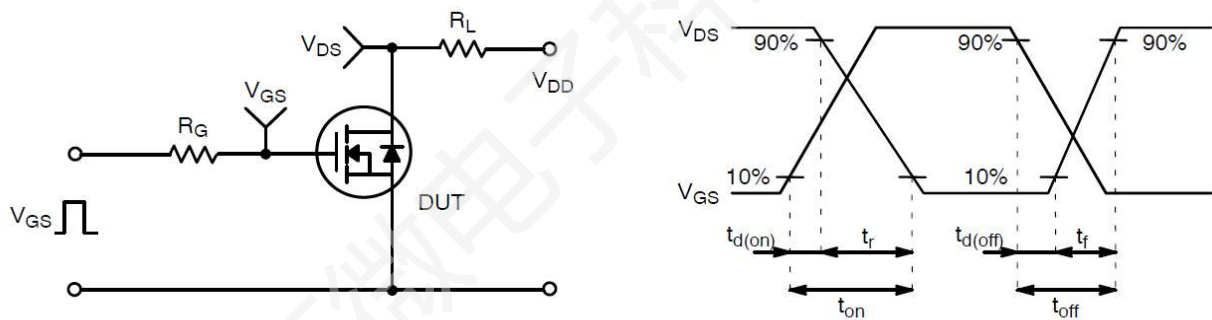
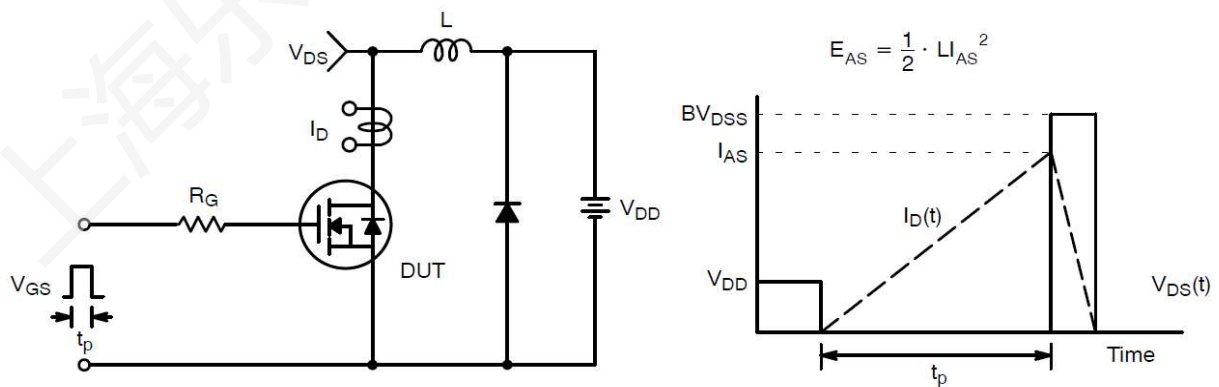
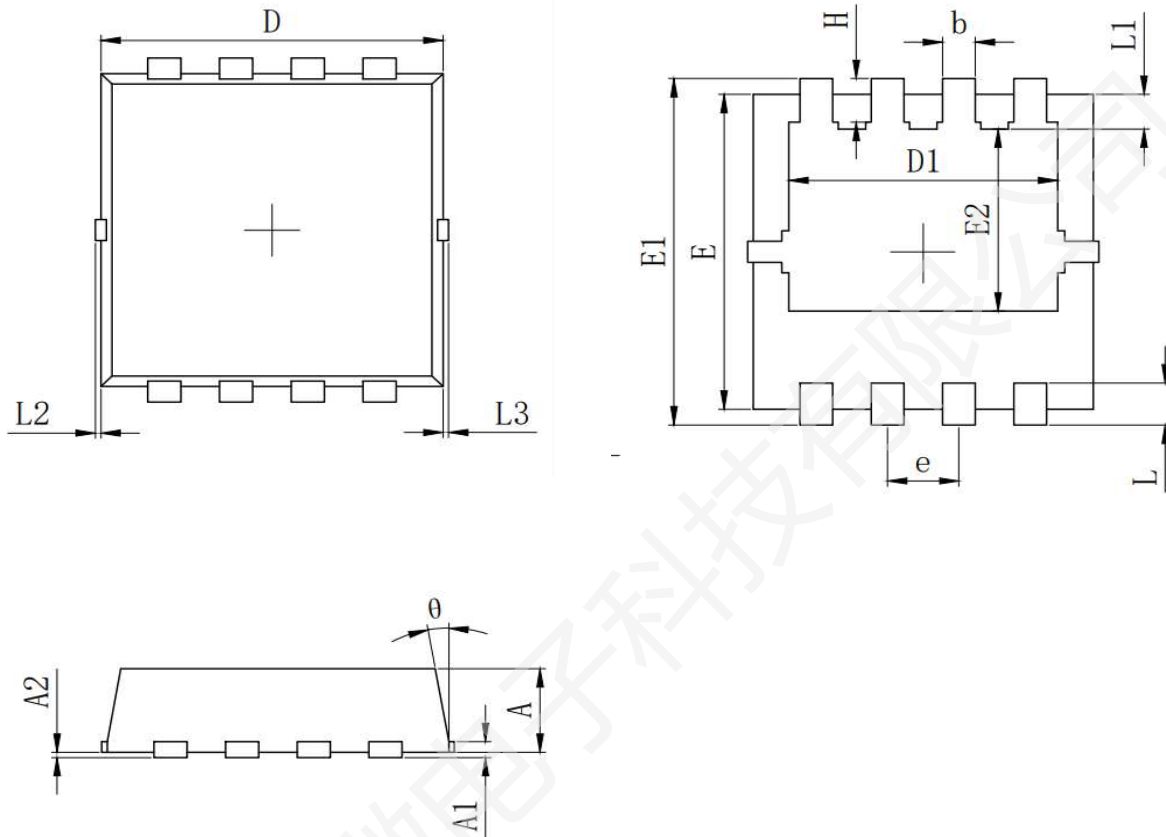


Figure 13: Max. Transient Thermal Impedance


Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


Symbol	MILLIMETER		
	Min	Nom	Max
A	0.700	0.800	0.900
A1	0.152 REF		
A2	0~0.05		
D	3.000	3.100	3.200
D1	2.300	2.450	2.600
E	2.900	3.000	3.100
E1	3.150	3.300	3.450
E2	1.535	1.735	1.935
b	0.200	0.300	0.400
e	0.550	0.650	0.750
L	0.300	0.400	0.500
L1	0.180	0.330	0.480
L2	0~0.100		
L3	0~0.100		
H	0.315	0.415	0.515
θ	8°	10°	12°

Revision History:

Revision	Date	Descriptions
Rev 1.1	July.2025	Initial Version
Rev 1.2	Sep.2025	Ectable update

Disclaimer:

The information in this document is believed to be accurate and reliable. However, no responsibility is assumed by LW-Micro for its use. All operating parameters must be designed, validated and tested to ensure they meet the requirements of your application. LW-Micro reserves the right to make any specification and/or circuitry changes without prior notification. Before starting a brand-new project, please contact LW-Micro Sales to get the most recent relevant information.

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